

Andrei Vescan

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Zero-Bias Power-Detector Circuits based on MoS ₂ Field-Effect Transistors on Wafer-Scale Flexible Substrates. <i>Advanced Materials</i> , 2022, 34, e2108469.	11.1	14
2	NEUROTEC I: Neuro-inspired Artificial Intelligence Technologies for the Electronics of the Future. , 2022, , .		0
3	Detailed study on MOCVD of wafer-scale MoS ₂ monolayers: From nucleation to coalescence. <i>MRS Advances</i> , 2022, 7, 751-756.	0.5	6
4	Selective-area growth study of GaN micropillars for quasi-vertical Schottky diodes. <i>Semiconductor Science and Technology</i> , 2021, 36, 034005.	1.0	0
5	Showerhead-assisted chemical vapor deposition of CsPbBr ₃ films for LED applications. <i>Journal of Materials Research</i> , 2021, 36, 1813-1823.	1.2	8
6	Transfer-free, scalable photodetectors based on MOCVD-grown 2D-heterostructures. <i>2D Materials</i> , 2021, 8, 045015.	2.0	8
7	AlGaIn/GaN high electron mobility transistor oscillator for high temperature and high frequency. <i>Electronics Letters</i> , 2021, 57, 148-150.	0.5	1
8	GaN Micropillar Schottky Diodes with High Breakdown Voltage Fabricated by Selective-Area Growth. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020, 217, 1900676.	0.8	4
9	Limitations for Reliable Operation at Elevated Temperatures of Al ₂ O ₃ /AlGaIn/GaN Metal-Insulator-Semiconductor High-Electron-Mobility Transistors Grown by Metal-Organic Chemical Vapor Deposition on Silicon Substrate. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020, 217, 1900697.	0.8	2
10	Flexible Large-Area Light-Emitting Devices Based on WS ₂ Monolayers. <i>Advanced Optical Materials</i> , 2020, 8, 2000694.	3.6	32
11	Evaluation of High-Temperature High-Frequency GaN-Based LC-Oscillator Components. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 4587-4591.	1.6	5
12	MOVPE of Large-Scale MoS ₂ /WS ₂ , WS ₂ /MoS ₂ , WS ₂ /Graphene and MoS ₂ /Graphene 2D-2D Heterostructures for Optoelectronic Applications. <i>MRS Advances</i> , 2020, 5, 1625-1633.	0.5	10
13	Analysis of an AlGaIn/AlN Super-Lattice Buffer Concept for 650-V Low-Dispersion and High-Reliability GaN HEMTs. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 1113-1119.	1.6	27
14	High-Intensity CsPbBr ₃ Perovskite LED using Poly(bis(4-phenyl)(2,4,6-trimethylphenyl)amine) as Hole Transport and Electron-Blocking Layer. <i>MRS Advances</i> , 2020, 5, 411-419.	0.5	3
15	Interplay between C-doping, threading dislocations, breakdown, and leakage in GaN on Si HEMT structures. <i>AIP Advances</i> , 2020, 10, .	0.6	15
16	Showerhead-Assisted Chemical Vapor Deposition of Perovskite Films for Solar Cell Application. <i>MRS Advances</i> , 2020, 5, 385-393.	0.5	2
17	Highly Responsive Flexible Photodetectors Based on MOVPE Grown Uniform Few-Layer MoS ₂ . <i>ACS Photonics</i> , 2020, 7, 1388-1395.	3.2	60
18	Scalable Large-Area p-i-n Light-Emitting Diodes Based on WS ₂ Monolayers Grown via MOCVD. <i>ACS Photonics</i> , 2019, 6, 1832-1839.	3.2	36

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19	Extraction of the active acceptor concentration in (pseudo-) vertical GaN MOSFETs using the body-bias effect. <i>Microelectronics Journal</i> , 2019, 91, 42-45.	1.1	7
20	Chemical Vapor Deposition of Organic-Inorganic Bismuth-Based Perovskite Films for Solar Cell Application. <i>Scientific Reports</i> , 2019, 9, 9774.	1.6	45
21	Fabrication of Methylammonium Bismuth Iodide Layers Employing Methylamine Vapor Exposure. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1900169.	0.8	8
22	Development of a III-nitride electro-optical modulator for UV-vis. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SCCC04.	0.8	4
23	High-mobility GaN-on-sapphire p-n diodes with near-unity ideality factor and large breakdown voltage. <i>Journal Physics D: Applied Physics</i> , 2019, 52, 285101.	1.3	6
24	Comparison of MOCVD and MBE Regrowth for CAVET Fabrication. <i>Electronics (Switzerland)</i> , 2019, 8, 377.	1.8	10
25	Optimization of Transparent Organic Light-Emitting Diodes by Simulation-Based Design of Organic Capping Layers. <i>Journal of Nanoscience and Nanotechnology</i> , 2019, 19, 3959-3963.	0.9	4
26	Reaction engineering of CVD methylammonium bismuth iodide layers for photovoltaic applications. <i>Journal of Materials Research</i> , 2019, 34, 608-615.	1.2	9
27	H ₂ S-free Metal-Organic Vapor Phase Epitaxy of Coalesced 2D WS ₂ Layers on Sapphire - ERRATUM. <i>MRS Advances</i> , 2019, 4, e1-e1.	0.5	3
28	Growth and Characterization of Vertical and Lateral p-n Junctions Formed by Selective-Area GaN MOVPE on Patterned Templates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1800677.	0.8	10
29	H ₂ S-free Metal-Organic Vapor Phase Epitaxy of Coalesced 2D WS ₂ Layers on Sapphire. <i>MRS Advances</i> , 2019, 4, 593-599.	0.5	13
30	Improved luminescence properties of MoS ₂ monolayers grown via MOCVD: role of pre-treatment and growth parameters. <i>Nanotechnology</i> , 2018, 29, 295704.	1.3	23
31	Impact of AlN/Si Nucleation Layers Grown Either by NH ₃ -MBE or MOCVD on the Properties of AlGaIn/GaN HFETs. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018, 215, 1700638.	0.8	0
32	Metalorganic Vapor-Phase Epitaxy Growth Parameters for Two-Dimensional MoS ₂ . <i>Journal of Electronic Materials</i> , 2018, 47, 910-916.	1.0	25
33	Demonstration of a GaN-Based Vertical-Channel JFET Fabricated by Selective-Area Regrowth. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 5329-5336.	1.6	32
34	Morphology Control of Organic-Inorganic Bismuth-Based Perovskites for Solar Cell Application. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018, 215, 1800409.	0.8	16
35	Fabrication and Characterization of Air-Stable Organic-Inorganic Bismuth-Based Perovskite Solar Cells. <i>MRS Advances</i> , 2018, 3, 3085-3090.	0.5	4
36	Self-Aligned Process for Selectively Etched p-GaN-Gated AlGaIn/GaN-on-Si HFETs. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 3732-3738.	1.6	42

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37	Investigation of Perovskite Solar Cells Employing Chemical Vapor Deposited Methylammonium Bismuth Iodide Layers. MRS Advances, 2018, 3, 3069-3074.	0.5	3
38	Effect of Carbon Doping Level on Static and Dynamic Properties of AlGaIn/GaN Heterostructures Grown on Silicon. IEEE Transactions on Electron Devices, 2018, 65, 3192-3198.	1.6	28
39	Nitride Semiconductors. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1800301.	0.8	0
40	Zirconium Tetrakis(8-hydroxyquinolinolate) and Lithium Schiff-Base Cluster Complex for Efficient Charge Injection and Transfer in Green PHOLED processed by OVPD. MRS Advances, 2018, 3, 3471-3476.	0.5	0
41	Effect of Different Carbon Doping Techniques on the Dynamic Properties of GaN-on-Si Buffers. IEEE Transactions on Electron Devices, 2017, 64, 991-997.	1.6	31
42	Direct Chemical Vapor Phase Deposition of Organometal Halide Perovskite Layers. MRS Advances, 2017, 2, 1189-1194.	0.5	6
43	Backside Contacting for Uniform Luminance in Large-Area OLED. MRS Advances, 2017, 2, 2275-2280.	0.5	0
44	Simplified efficient phosphorescent organic light-emitting diodes by organic vapor phase deposition. Applied Physics Letters, 2017, 111, 243301.	1.5	3
45	Large-area MoS ₂ deposition via MOVPE. Journal of Crystal Growth, 2017, 464, 100-104.	0.7	30
46	Transparent Ag-Free OLED Fabricated by OVPD Using Thin Au Contacts. MRS Advances, 2016, 1, 477-482.	0.5	0
47	Effect of stress voltage on the dynamic buffer response of GaN-on-silicon transistors. Journal of Applied Physics, 2016, 119, .	1.1	17
48	Limitations of threshold voltage engineering of AlGaIn/GaN heterostructures by dielectric interface charge density and manipulation by oxygen plasma surface treatments. Journal of Applied Physics, 2016, 119, .	1.1	5
49	Pseudo-vertical GaN-based trench gate metal oxide semiconductor field effect transistor. , 2016, , .		0
50	Investigation of organic semiconductor interlayers in hybrid PEDOT:PSS/silicon solar cells. Journal of Photonics for Energy, 2016, 6, 045503.	0.8	1
51	Optimization of hybrid organic/inorganic poly(3-hexylthiophene-2,5-diyl)/silicon solar cells. Journal of Photonics for Energy, 2016, 6, 025504.	0.8	2
52	Influence of Band Tailing on Photo- and Electroluminescence Polarization of m-Plane InGaIn/GaN Quantum Well Heterostructures. Journal of Applied Spectroscopy, 2016, 82, 956-960.	0.3	1
53	Optical and structural properties of GaN epitaxial layers on LiAlO ₂ substrates and their correlation with basal-plane stacking faults. Journal of Crystal Growth, 2016, 434, 62-66.	0.7	4
54	The III-Nitride Double Heterostructure Revisited: Benefits for Threshold Voltage Engineering of MIS Devices. IEEE Transactions on Electron Devices, 2016, 63, 606-613.	1.6	14

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55	Low-Temperature Processed Hybrid Organic/Silicon Solar Cells with Power Conversion Efficiency up to 6.5%. Materials Research Society Symposia Proceedings, 2015, 1771, 201-206.	0.1	3
56	Investigations of the electrochemical stability of InGaN photoanodes in different electrolytes. Physica Status Solidi (B): Basic Research, 2015, 252, 895-899.	0.7	6
57	Advanced thin-film chip concepts for efficient InGaN solar cells. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 2053-2058.	0.8	0
58	Semi-polar Γ blue and green InGaN/GaN light-emitting diodes on micro-stripe patterned Si (100). Journal Physics D: Applied Physics, 2015, 48, 485103.	1.3	13
59	The effect of AlN nucleation growth conditions on the inversion channel formation at the AlN/silicon interface. , 2015, , .		5
60	The controlled growth of GaN microrods on Si(111) substrates by MOCVD. Journal of Crystal Growth, 2015, 414, 200-204.	0.7	11
61	Threshold Voltage Engineering in GaN-Based HFETs: A Systematic Study With the Threshold Voltage Reaching More Than 2 V. IEEE Transactions on Electron Devices, 2015, 62, 538-545.	1.6	23
62	Effect of antimony on growth mode and properties of thick InGaN layers. Journal of Crystal Growth, 2015, 414, 42-48.	0.7	4
63	AlGaN/AlN-GaN-SL HEMTs with Multiple 2DEG Channels. Journal of Electronic Materials, 2015, 44, 1263-1267.	1.0	4
64	Charge balancing in GaN-based 2-D electron gas devices employing an additional 2-D hole gas and its influence on dynamic behaviour of GaN-based heterostructure field effect transistors. Journal of Applied Physics, 2015, 117, .	1.1	21
65	Controlling the interface charge density in GaN-based metal-oxide-semiconductor heterostructures by plasma oxidation of metal layers. Journal of Applied Physics, 2015, 117, 214503.	1.1	3
66	Fabrication of p-channel heterostructure field effect transistors with polarization-induced two-dimensional hole gases at metal/polar GaN/AlInGaN interfaces. Journal Physics D: Applied Physics, 2014, 47, 175103.	1.3	67
67	Characterization of GaN-based p-channel device structures at elevated temperatures. Semiconductor Science and Technology, 2014, 29, 075002.	1.0	9
68	Novel GaN-based transistors using polarization engineering. , 2014, , .		0
69	Pentacene/K12 solar cells formed by organic vapor phase deposition. Journal of Photonics for Energy, 2014, 4, 043092.	0.8	0
70	Improved Light Outcoupling from OLED by Non-Wave-Guiding Anode Designs. Materials Research Society Symposia Proceedings, 2014, 1627, 1.	0.1	1
71	The effect of the inversion channel at the AlN/Si interface on the vertical breakdown characteristics of GaN-based devices. Semiconductor Science and Technology, 2014, 29, 115012.	1.0	60
72	Selective MOVPE of InGaN-based LED structures on non-planar Si (111) facets of patterned Si (100) substrates. Journal of Crystal Growth, 2014, 391, 33-40.	0.7	11

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73	In-situ decomposition and etching of AlN and GaN in the presence of HCl. Journal of Crystal Growth, 2014, 393, 89-92.	0.7	5
74	Strain relief mechanisms and growth behavior of superlattice distributed Bragg reflectors. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 758-761.	0.8	0
75	InGaN: Direct correlation of nanoscopic morphology features with optical and structural properties. Applied Physics Letters, 2014, 105, 072108.	1.5	6
76	First monolithic integration of GaN-based enhancement mode n-channel and p-channel heterostructure field effect transistors. , 2014, , .		35
77	Growth properties and electrochemical characterization of InGaN photoanodes with different In concentrations. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 746-749.	0.8	3
78	Investigation of large-area OLED devices with various grid geometries. Organic Electronics, 2013, 14, 2387-2391.	1.4	28
79	AlGaIn/GaN heterostructure field-effect transistors regrown on nitrogen implanted templates. Semiconductor Science and Technology, 2013, 28, 085006.	1.0	1
80	Power Performance at 40 GHz on Quaternary Barrier InAlGaIn/GaN HEMT. IEEE Electron Device Letters, 2013, 34, 978-980.	2.2	36
81	p-Channel Enhancement and Depletion Mode GaN-Based HFETs With Quaternary Backbarriers. IEEE Transactions on Electron Devices, 2013, 60, 3005-3011.	1.6	61
82	Evaluation of interpolations of InN, AlN and GaN lattice and elastic constants for their ternary and quaternary alloys. Journal Physics D: Applied Physics, 2013, 46, 245502.	1.3	19
83	HCl-assisted growth of GaN and AlN. Journal of Crystal Growth, 2013, 370, 30-35.	0.7	3
84	Polarization-Engineered Enhancement-Mode High-Electron-Mobility Transistors Using Quaternary AlInGaIn Barrier Layers. Journal of Electronic Materials, 2013, 42, 826-832.	1.0	36
85	Insulating behavior of interfaces in regrown Al _{0.23} Ga _{0.77} N/GaN double heterostructures on Al _{0.07} Ga _{0.93} N back-barrier templates. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 799-802.	0.8	3
86	Enhancement mode InAlGaIn/GaN MISHFETs with plasma-oxidised AlO _x /TiO _x gate insulator. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 840-843.	0.8	2
87	MOVPE growth, optical and electrical characterization of thick Mg-doped InGaIn layers. Journal of Crystal Growth, 2013, 370, 2-6.	0.7	4
88	Electron channeling contrast imaging studies of nonpolar nitrides using a scanning electron microscope. Applied Physics Letters, 2013, 102, .	1.5	16
89	AlN barrier HFETs with AlGaIn channels to shift the threshold voltage to higher positive values: a proposal. Semiconductor Science and Technology, 2013, 28, 074017.	1.0	22
90	Temperature-resolved photoluminescence of nonpolar InGaIn/GaN multiple quantum well heterostructures grown on LiAlO ₂ . Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 532-535.	0.8	0

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91	GaN-on-Si Enhancement Mode Metal Insulator Semiconductor Heterostructure Field Effect Transistor with On-Current of 1.35 A/mm. Japanese Journal of Applied Physics, 2013, 52, 090204.	0.8	13
92	Characterization of charge injection and photovoltaic effects of hybrid inorganic-organic GaN/pentacene heterostructures. Applied Physics Letters, 2013, 103, .	1.5	5
93	First Small-Signal Data of GaN-Based p-Channel Heterostructure Field Effect Transistors. Japanese Journal of Applied Physics, 2013, 52, 128001.	0.8	10
94	Formation of a Monocrystalline, γ -Plane AlN Layer by the Nitridation of γ -LiAlO ₂ (100). Applied Physics Express, 2012, 5, 105501.	1.1	5
95	Investigation of plasma-oxidized aluminium as a gate dielectric for AlGaN/GaN MISHFETs. Semiconductor Science and Technology, 2012, 27, 062001.	1.0	10
96	Polarization-reduced quaternary InAlGaN/GaN HFET and MISHFET devices. Semiconductor Science and Technology, 2012, 27, 055012.	1.0	9
97	Influence of mask material and process parameters on etch angle in a chlorine-based GaN dry etch. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2012, 30, .	0.9	13
98	Quaternary nitride enhancement mode HFET with 260 mS/mm and a threshold voltage of +0.5 V. , 2012, , .		5
99	Relaxation and critical strain for maximum In incorporation in AlInGaN on GaN grown by metal organic vapour phase epitaxy. Journal of Applied Physics, 2012, 112, 093524.	1.1	18
100	The effect of gate length variation on InAlGaN/GaN HFET device characteristics. Semiconductor Science and Technology, 2012, 27, 035009.	1.0	3
101	First polarization-engineered compressively strained AlInGaN barrier enhancement-mode MISHFET. Semiconductor Science and Technology, 2012, 27, 055004.	1.0	26
102	Electrical properties of quasi-vertical Schottky diodes. Semiconductor Science and Technology, 2012, 27, 085015.	1.0	24
103	Structural, electrical and optical characterization of MOCVD grown In-rich InGaN layers. Journal of Crystal Growth, 2012, 358, 51-56.	0.7	6
104	Characterization of charge carrier injection in organic and hybrid organic/inorganic semiconductor devices by capacitance-voltage measurements. , 2012, , .		2
105	Modelling of hole transport in a small-molecule organic material assuming carrier heating in a Gaussian density of states. , 2012, , .		1
106	Highly n-type doped InGaN films for efficient direct solar hydrogen generation. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 964-967.	0.8	6
107	Growth Studies on Quaternary AlInGaN Layers for HEMT Application. Journal of Electronic Materials, 2012, 41, 905-909.	1.0	20
108	Oxygen addition to fluorine based SiN etch process: Impact on the electrical properties of AlGaN/GaN 2DEG and transistor characteristics. Solid-State Electronics, 2012, 67, 90-93.	0.8	9

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109	Quaternary Enhancement-Mode HFET With In Situ SiN Passivation. IEEE Electron Device Letters, 2012, 33, 519-521.	2.2	10
110	RF performance of InAlN/AlN/GaN HEMTs on sapphire substrate. Electronics Letters, 2011, 47, 212.	0.5	10
111	Strong charge carrier localization interacting with extensive nonradiative recombination in heteroepitaxially grown m-plane GaInN quantum wells. Semiconductor Science and Technology, 2011, 26, 105017.	1.0	10
112	InAlN/GaN HEMTs on Sapphire Substrate With 2.9-W/mm Output Power Density at 18 GHz. IEEE Electron Device Letters, 2011, 32, 1537-1539.	2.2	31
113	Dielectric function and optical properties of quaternary AlInGaN alloys. Journal of Applied Physics, 2011, 110, .	1.1	31
114	On the thermal oxidation of AlInN/AlN/GaN heterostructures. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2213-2215.	0.8	6
115	Growth of GaN in a planetary MOCVD hotwall system. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2041-2043.	0.8	3
116	Electrothermal characterization of large-area organic light-emitting diodes employing finite-element simulation. Organic Electronics, 2011, 12, 1399-1405.	1.4	30
117	On the anisotropic wafer curvature of GaN-based heterostructures on Si(110) substrates grown by MOVPE. Journal of Crystal Growth, 2011, 315, 220-223.	0.7	8
118	High-excitation luminescence properties of m-plane GaN grown on LiAlO ₂ substrates. Journal of Crystal Growth, 2011, 329, 33-38.	0.7	2
119	Irregular spectral position of E _c component of polarized photoluminescence from m-plane InGaN/GaN multiple quantum wells grown on LiAlO ₂ . Applied Physics Letters, 2011, 99, 232114.	1.5	5
120	Electrical properties of thermally oxidized AlInN/AlN/GaN-based metal oxide semiconductor hetero field effect transistors. Journal of Applied Physics, 2011, 110, .	1.1	16
121	Recessed-Gate Enhancement-Mode AlGaIn/GaN Heterostructure Field-Effect Transistors on Si with Record DC Performance. Applied Physics Express, 2011, 4, 114102.	1.1	73
122	Impact of gate dielectric thickness on the electrical properties of AlGaIn/GaN MISHFETs on Si(111) substrate. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1342-1344.	0.8	5
123	In situ SiN passivation of AlInN/GaN heterostructures by MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2104-2106.	0.8	9
124	Quaternary nitride heterostructure field effect transistors. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2001-2003.	0.8	10
125	Study on quaternary AlInGaIn/GaN HFETs grown on sapphire substrates. Semiconductor Science and Technology, 2010, 25, 075013.	1.0	62
126	Fusion of intraoperative cone-beam CT and endoscopic video for image-guided procedures. , 2010, , .		24

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127	Characterization of AlGaIn/GaN MISHFETs on a Si substrate by static and high-frequency measurements. Semiconductor Science and Technology, 2009, 24, 075014.	1.0	10
128	Study on growth and electrical performance of double-heterostructure AlGaIn/GaN/AlGaIn field-effect transistors. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S1003.	0.8	6
129	Processing approaches of AlGaIn/GaN Metal Insulator Semiconductor Hetero Field Effect Transistors (MISHFET) on Si (111) substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S1033-S1036.	0.8	5
130	Influence of barrier thickness on AlInN/AlN/GaN heterostructures and device properties. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S1041.	0.8	13
131	Epitaxy and characterisation of AlInGaIn heterostructures for HEMT application. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S470.	0.8	6
132	AlInN/GaN HEMTs on sapphire: dc and pulsed characterisation. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1926-1928.	0.8	2
133	Optimisation of AlInN/GaN HEMT structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2041-2043.	0.8	13
134	Investigation of trapping effects in AlGaIn/GaN/Si field-effect transistors by frequency dependent capacitance and conductance analysis. Applied Physics Letters, 2008, 93, 124103.	1.5	95
135	Advanced Modeling of MISHFET Devices and their Performance in Current-Mode Class-D Power Amplifiers. , 2008, , .		0
136	Processing and characterization of recessed-gate AlGaIn/GaN HFETs. , 2008, , .		1
137	MOVPE, processing and characterization of AlGaIn/GaN HEMTs with different Al concentrations on silicon substrates. Journal of Crystal Growth, 2007, 298, 843-847.	0.7	11
138	Advanced buffers for AlGaIn/GaN HEMT and InGaIn/GaN MQW on silicon substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 2342-2345.	0.8	4
139	12 W/mm AlGaIn-GaN HFETs on Silicon Substrates. IEEE Electron Device Letters, 2004, 25, 459-461.	2.2	195
140	Power handling limits and degradation of large area AlGaIn/GaN RF-HEMTs. Solid-State Electronics, 2003, 47, 123-125.	0.8	9
141	AlGaIn/GaN HFETs on 100 mm Silicon Substrates for Commercial Wireless Applications. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 52-56.	0.8	22
142	Diamond diodes and transistors. Semiconductor Science and Technology, 2003, 18, S59-S66.	1.0	50
143	AlGaIn/GaN HFETs fabricated on 100-mm GaN on silicon () substrates. Solid-State Electronics, 2002, 46, 1535-1539.	0.8	102
144	Heat-spreading diamond films for GaN-based high-power transistor devices. Diamond and Related Materials, 2001, 10, 744-749.	1.8	73

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145	Current instabilities in GaN-based devices. IEEE Electron Device Letters, 2001, 22, 62-64.	2.2	142
146	Small signal and power measurements of AlGaIn/GaN HEMT with SiN passivation. Electronics Letters, 2001, 37, 130.	0.5	44
147	AlGaIn/GaN MODFETs on semi-insulating SiC with 3 W/mm at 20 GHz. Electronics Letters, 2000, 36, 1234.	0.5	15
148	Current limitation after pinch-off in AlGaIn/GaN FETs. MRS Internet Journal of Nitride Semiconductor Research, 2000, 5, 1.	1.0	21
149	MBE grown AlGaIn/GaN MODFETs with high breakdown voltage. Journal of Crystal Growth, 1999, 201-202, 327-331.	0.7	10
150	$\hat{\Gamma}$ -Doping in diamond. Carbon, 1999, 37, 787-791.	5.4	47
151	Effect of Illumination on the Electrical Characteristics of AlGaIn/GaN FETs. Physica Status Solidi A, 1999, 176, 209-212.	1.7	11
152	Diamond junction FETs based on $\hat{\Gamma}$ -doped channels. Diamond and Related Materials, 1999, 8, 941-945.	1.8	73
153	Actuator - sensor technology on "electronic grade" diamond films. Microsystem Technologies, 1998, 5, 38-43.	1.2	11
154	High temperature, high voltage operation of diamond Schottky diode. Diamond and Related Materials, 1998, 7, 581-584.	1.8	72
155	Application of highly oriented, planar diamond (HOD) films of high mechanical strength in sensor technologies. Diamond and Related Materials, 1998, 7, 779-782.	1.8	22
156	Devices at High Temperatures – Status and Prospects. Israel Journal of Chemistry, 1998, 38, 105-112.	1.0	1
157	First diamond power FET structure. , 1997, , .		3
158	High-temperature, high-voltage operation of pulse-doped diamond MESFET. IEEE Electron Device Letters, 1997, 18, 222-224.	2.2	45
159	Diamond surface-channel FET structure with 200 V breakdown voltage. IEEE Electron Device Letters, 1997, 18, 547-549.	2.2	99
160	Very high temperature operation of diamond Schottky diode. IEEE Electron Device Letters, 1997, 18, 556-558.	2.2	67
161	High-voltage Schottky diode on epitaxial diamond layer. Diamond and Related Materials, 1997, 6, 329-332.	1.8	48
162	Electrical characterisation of diamond resistors etched by RIE. Diamond and Related Materials, 1996, 5, 747-751.	1.8	26

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